





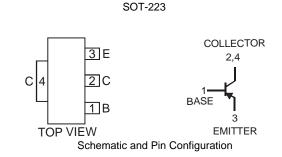
LOW V<sub>CE(SAT)</sub> PNP SURFACE MOUNT TRANSISTOR

#### **Features**

- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

#### Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.115 grams (approximate)



#### **Maximum Ratings** $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-140	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	Ι <sub>C</sub>	-4	А
Peak Pulse Current	I <sub>CM</sub>	-10	А

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ $T_A = 25^{\circ}C$	PD	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^{\circ}C$	$R_{\theta JA}$	125	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 1. No purposefully added lead.

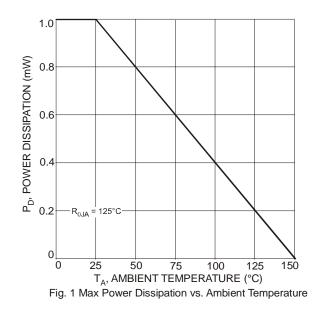
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.

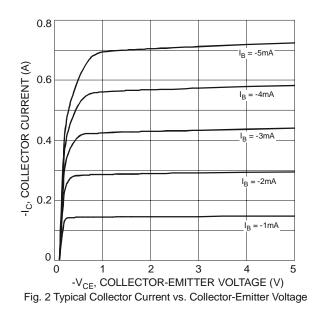
3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	-180	_	_	V	$I_{C} = -100 \mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	-140		_	V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	-6	_	_	V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	—	-50 -1	nA μA	
Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-10	nA	$V_{EB} = -6V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)						
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_		-60 -120	mV	$I_{C} = -100$ mA, $I_{B} = -5$ mA $I_{C} = -500$ mA, $I_{B} = -50$ mA
		_		-150 -370	IIIV	$I_{C} = -1A, I_{B} = -100mA$ $I_{C} = -3A, I_{B} = -300mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_		-1110	mV	$I_{C} = -3A, I_{B} = -300mA$
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>	_		-950	mV	$I_{C} = -3A, V_{CE} = -5V$
DC Current Gain	h <sub>FE</sub>	100 100 75	— — — 10	300 —	_	$I_{C} = -10mA, V_{CE} = -5V$ $I_{C} = -1A, V_{CE} = -5V$ $I_{C} = -3A, V_{CE} = -5V$ $I_{C} = -10A, V_{CF} = -5V$
SMALL SIGNAL CHARACTERISTICS			10			$1_{\rm C} = -10$ $, v_{\rm CE} = -5$ $v$
Current Gain-Bandwidth Product	f <sub>T</sub>	_	150	_	MHz	$I_{C} = -100 \text{mA}, V_{CE} = -10 \text{V}, f = 100 \text{MHz}$
Output Capacitance	C <sub>obo</sub>	_	40	_	pF	$V_{CB} = -20V, f = 1MHz$
SWITCHING CHARACTERISTICS						
Switching Times	t <sub>on</sub> t <sub>off</sub>	_	85 430		ns	$I_{C} = -1A, I_{B1} = -100mA$ $I_{B2} = 100mA, V_{CC} = -50V$

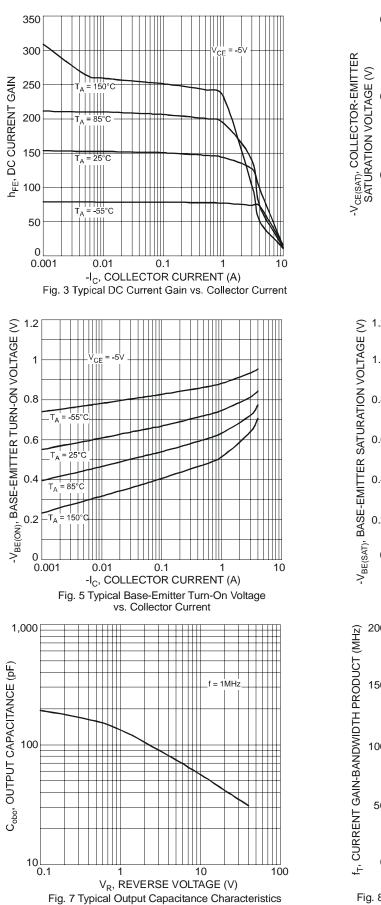
Notes: 4. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .







NEW PRODUCT



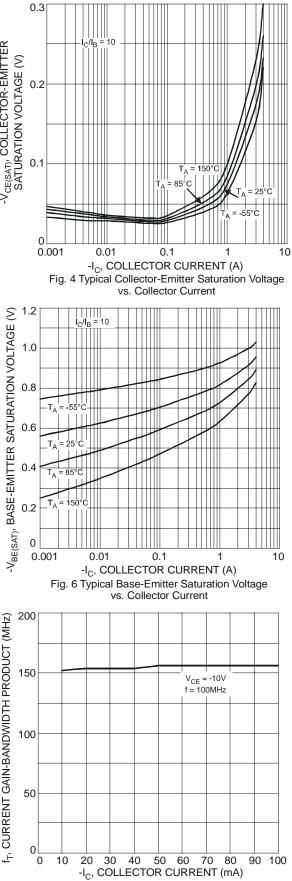


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

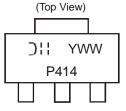


## Ordering Information (Note 5)

Device	Packaging	Shipping
DZT955-13	SOT-223	2500/Tape & Reel

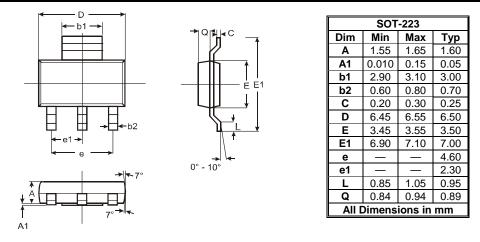
Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap02007.pdf.

#### **Marking Information**

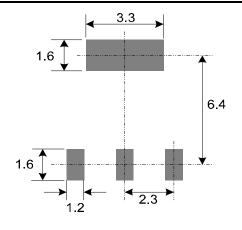


P414 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007WW = Week code 01 - 52

# **Package Outline Dimensions**



## Suggested Pad Layout: (Dimensions in mm)



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